

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A semiconductor device, comprising:

a first transistor including a first gate formed on a semiconductor substrate, a first low impurity concentration diffusion layer formed on the surface of said semiconductor substrate in a manner to surround said first gate, a first high impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said first low impurity concentration diffusion layer and to have a shallower diffusion depth than a diffusion depth of said first low impurity concentration diffusion layer, and a first gate side wall formed to surround the first gate with a top surface of the first gate being exposed from an upper end of the first gate side wall, and an interface between the first low impurity concentration diffusion layer and the first high impurity concentration diffusion layer corresponding to a lower end of an outer surface of the first gate side wall; and

a second transistor including a second gate formed on the semiconductor substrate, a second low impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said second gate, a second high impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said second low impurity concentration diffusion layer and to have a shallower diffusion depth than a diffusion depth of said second low impurity concentration diffusion layer, and a second gate side wall formed to surround said second gate and having a thickness equal to

that of the first gate side wall of said first transistor, a top surface of the second gate being exposed from an upper end of the second gate side wall;

wherein the size of said second low impurity concentration diffusion layer formed on the surface of the semiconductor substrate, which extends from said second gate to reach said second high impurity concentration diffusion layer, is larger than the size of said first low impurity concentration diffusion layer formed on the surface of the semiconductor substrate, which extends from said ~~second~~ first gate to reach said ~~second~~ first high impurity concentration diffusion layer, ~~and a~~ an effective lower end of an outer surface of the second gate side wall being positioned within a surface region of the second low impurity concentration diffusion layer ~~apart from an interface between the second low impurity concentration diffusion layer and~~ outside of a surface region of the second high impurity concentration diffusion layer, said first low impurity concentration diffusion layer is an N-type diffusion layer having a low impurity concentration, said first high impurity concentration diffusion layer is an N-type diffusion layer having a high impurity concentration said first transistor is an N-type transistor, said second low impurity concentration diffusion layer is a P-type diffusion layer having a low impurity concentration, said second low impurity concentration diffusion layer is a P-type diffusion layer having a low impurity concentration, and said second transistor is a P-type transistor.

Claim 2 (Canceled)

Claim 3 (Currently Amended): The A semiconductor device according to Claim 2, further comprising:

a first transistor including a first gate formed on a semiconductor substrate, a first low

impurity concentration diffusion layer formed on the surface of said semiconductor substrate in a manner to surround said first gate, a first high impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said first low impurity concentration diffusion layer, and a first gate side wall formed to surround the first gate with a top surface of the first gate being exposed from an upper end of the first gate side wall, and an interface between the first low impurity concentration diffusion layer and the first high impurity concentration diffusion layer corresponding to a lower end of an outer surface of the first gate side wall;

a second transistor including a second gate formed on the semiconductor substrate, a second low impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said second gate, a second high impurity concentration diffusion layer formed on the surface of the semiconductor substrate in a manner to surround said second low impurity concentration diffusion layer, and a second gate side wall formed to surround said second gate and having a thickness equal to that of the first gate side wall of said first transistor, a top surface of the second gate being exposed from an upper end of the second gate side wall; and

a third N-type transistor and fourth P-type transistor,

wherein said first and second transistors perform the function of a high voltage transistor,

the size of said second low impurity concentration diffusion layer formed on the surface of the semiconductor substrate, which extends from said second gate to reach said second high impurity concentration diffusion layer, is larger than the size of said first low

impurity concentration diffusion layer formed on the surface of the semiconductor substrate, which extends from said first gate to reach said first high impurity concentration diffusion layer, and a lower end of an outer surface of the second gate side wall being positioned within a surface region of the second low impurity concentration diffusion layer apart from an interface between the second low impurity concentration diffusion layer and the second high impurity concentration diffusion layer, said first low impurity concentration diffusion layer is an N-type diffusion layer having a low impurity concentration, said first high impurity concentration diffusion layer is an N-type diffusion layer having a high impurity concentration, said first transistor is an N-type transistor, said second low impurity concentration diffusion layer is a P-type diffusion layer having a low impurity concentration, and said second transistor is a P-type transistor, and

said third and fourth transistors perform the function of a low voltage transistor.

Claim 4 (Original): The semiconductor device according to Claim 1, further comprising a memory cell transistor including a third gate formed on said semiconductor substrate, a third diffusion layer having a high impurity concentration and formed within said semiconductor substrate around said third gate, and third gate side wall formed around said third gate and having a thickness substantially equal to those of said first and second gate side walls.

Claim 5 (Original): The semiconductor device according to Claim 3, further comprising a memory cell transistor including a third gate formed on said semiconductor substrate, a third diffusion layer having a high impurity concentration and formed within said semiconductor substrate around said third gate, and a third gate side wall formed around said

third gate and having a thickness substantially equal to those of said first and second gate side walls.

Claim 6 (Original): The semiconductor device according to Claim 5, wherein the third gate of said memory cell transistor includes a floating gate acting as a charge accumulating layer, a control gate formed above said floating gate, and an insulating layer interposed between said floating gate and said control gate.

Claim 7 (Original): The semiconductor device according to Claim 5, wherein said memory cell transistor is a nonvolatile memory device, said first transistor is an N-type MOS transistor having a first LDD structure, and said second transistor is a P-type MOS transistor having a second LDD structure, said second LDD structure being longer than said first LDD structure.

Claim 8 (Withdrawn): A method of manufacturing a semiconductor device, comprising:

forming a gate of a first transistor and a gate of a second transistor on a semiconductor substrate;

forming a first diffusion layer having a low impurity concentration in said semiconductor substrate with the gate of said first transistor used as a mask;

forming a second diffusion layer having a low impurity concentration in said semiconductor substrate with the gate of said second transistor used as a mask;

forming gate side walls of the same thickness to surround the gates of said first transistor and said second transistor, respectively;

forming a first diffusion layer having a high impurity concentration, which is

positioned adjacent to said first diffusion layer having a low impurity concentration, within said semiconductor substrate, with the gate side wall of said first transistor used as a mask;

forming a mask side wall on the gate side wall of said second transistor;

forming a second diffusion layer having a high impurity concentration, which is positioned adjacent to said second diffusion layer having a low impurity concentration, within said semiconductor substrate, with the mask side wall used as a mask; and

removing said mask side wall.

Claim 9 (Withdrawn): The method of manufacturing a semiconductor device according to Claim 8, wherein said first diffusion layer having a low impurity concentration is an N-type diffusion layer having a low impurity concentration, said first diffusion layer having a high impurity concentration is an N-type diffusion layer having a high impurity concentration, said first transistor is an N-type transistor, said second diffusion layer having a low impurity concentration is a P-type diffusion layer having a low impurity concentration, said second diffusion layer having a low impurity concentration is a P-type diffusion layer having a high impurity concentration, and said second transistor is a P-type transistor.

Claim 10 (Withdrawn): The method of manufacturing a semiconductor device according to Claim 8, further comprising:

forming a third gate of the memory cell transistor on said semiconductor substrate;

forming a third diffusion layer having a high impurity concentration within said semiconductor substrate around said third gate; and

forming a third gate side wall substantially equal in thickness to said first and second gate side walls around said third gate.

Claim 11 (Withdrawn): The method of manufacturing a semiconductor device according to Claim 9, wherein a floating gate acting as a charge accumulating layer, a control gate positioned above said floating gate, and an insulating layer interposed between said floating gate and said control gate are formed as a third gate of said memory cell transistor.

Claim 12 (Withdrawn): The method of manufacturing a semiconductor device according to Claim 8, wherein said memory cell transistor is a nonvolatile memory device, said first transistor is an N-type MOS transistor having a first LDD structure, and said second transistor is a P-type MOS transistor having a second LDD structure, said second LDD structure being longer than said first LDD structure.

Claim 13 (Withdrawn): A method of manufacturing a semiconductor device according to Claim 8, comprising:

forming on the semiconductor substrate a gate of a high voltage PMOS transistor as said second transistor and a gate of a high voltage NMOS transistor as said first transistor;

forming an N⁻ diffusion layer within said semiconductor substrate with the gate of said high voltage NMOS transistor used as a mask;

forming said gate side walls substantially equal to each other in thickness on the gates of said high voltage PMOS transistor and said high voltage NMOS transistor;

forming an N⁺ diffusion layer within said semiconductor substrate with the gate side wall of said high voltage NMOS transistor used as a mask;

forming an P⁻ diffusion layer within said semiconductor substrate with the gate side wall of said high voltage PMOS transistor used as a mask;

forming said mask side walls substantially equal to each other in thickness on the first

side walls of said high voltage PMOS transistor and said high voltage NMOS transistor; and
forming a P⁺ diffusion layer within said semiconductor substrate by using the mask
side wall of said high voltage PMOS transistor.

Claim 14 (Withdrawn): A method of manufacturing a semiconductor device,
comprising:

forming a first gate insulating film for a high voltage transistor on a semiconductor
substrate;

forming a second gate insulating film for a low voltage transistor, said second gate
insulating film being thinner than said first gate insulating film;

forming a stacked gate structure by stacking conductive materials forming the gate
electrode, followed by selectively patterning by etching the stacked structure;

introducing an impurity of a first conductivity type into the semiconductor substrate;

depositing a first side wall material;

forming a first side wall on the side surface of said gate electrode by selectively
etching said first side wall material by means of an anisotropic etching;

introducing an impurity into a first MOS transistor region of the semiconductor
substrate in a concentration higher than that in an impurity diffusion layer of a second
conductivity type;

depositing a second side wall material and a third side wall material differing from
said second side wall material;

forming a third side wall on the side surface of said second side wall by selectively
etching said third side wall material by means of an anisotropic etching;

introducing an impurity of said first conductivity type into the second MOS transistor region of the semiconductor substrate with said third side wall used as a mask;

depositing an interlayer insulating film on the entire surface of said semiconductor substrate; and

selectively forming contact holes in said interlayer insulating film.

Claim 15 (Withdrawn): A method of manufacturing a semiconductor device, comprising:

forming an element isolating region in a semiconductor substrate;

forming a tunnel oxide film for a memory cell, a floating gate and an interlayer insulating film;

forming a first gate insulating film for a high voltage transistor on said semiconductor substrate;

forming a second gate insulating film for a low voltage transistor, said second gate insulating film being thinner than said first gate insulating film;

stacking conductive materials forming a control gate and a floating gate, followed by selectively patterning successively said control gate, said interlayer insulating film, and said floating gate;

selectively patterning the gate electrode in the peripheral circuit region;

introducing an impurity of a second conductivity type into the semiconductor substrate in the memory cell region and the peripheral circuit region;

depositing a first side wall material;

forming a first side wall on the side surface of said gate electrode by selectively

etching the first side wall material by an anisotropic etching;

introducing an impurity into the first MOS transistor region of the semiconductor substrate in a concentration higher than that in said impurity diffusion layer of the second conductivity type;

depositing a second side wall material and a third side wall material differing from said second side wall material;

forming a third side wall on the side surface of said second side wall by selectively etching said third side wall material by an anisotropic etching;

introducing an impurity of a first conductivity type into a second MOS transistor region of said semiconductor substrate with said third side wall used as a mask;

removing said third side wall;

depositing an interlayer insulating film on the entire surface of said semiconductor substrate;

selectively forming contact holes in said interlayer insulating film;

forming a metal wiring; and

forming an insulating film on said metal wiring.

Claim 16 (Withdrawn): A method of manufacturing a semiconductor device, comprising:

forming an element isolating region in a semiconductor substrate;

forming a first gate insulating film for a high voltage transistor on said semiconductor substrate;

forming a second gate insulating film for a low voltage transistor, said second gate

insulating film being thinner than said first gate insulating film;

stacking a conductive material layer forming a gate electrode, followed by patterning said conductive material layer by an etching;

introducing an impurity of a second conductivity type into a first MOS transistor region of the semiconductor substrate;

depositing a first side wall material;

forming a first side wall on the side surface of said gate electrode by selectively etching said first side wall material by an anisotropic etching;

introducing an impurity of a first conductivity type into a second MOS transistor region of the semiconductor substrate with said first side wall used as a mask;

introducing an impurity into the first MOS transistor region of the semiconductor substrate in a concentration higher than that in the diffusion layer of the second conductivity type;

depositing a second side wall material and a third side wall material differing from said second side wall material;

forming a third side wall on the side surface of said second side wall by selectively etching said third side wall material layer by an anisotropic etching;

introducing an impurity of the first conductivity type into a second MOS transistor region of the semiconductor substrate in a concentration higher than that in the impurity diffusion layer of the first conductivity type;

removing the third side wall;

depositing an interlayer insulating film on the entire substrate; and

selectively forming contact holes in said interlayer insulating film.

Claim 17 (Withdrawn): The method of manufacturing a semiconductor device according to Claim 16, further comprising:

forming on said semiconductor substrate an element isolating region, a tunnel oxide film for a memory cell device, a floating gate electrode for said memory cell device and an interlayer insulating film for said memory cell device;

forming at least a single layer of a metal wiring on said contact hole; and

forming an insulating film on said metal wiring.

Claim 18 (Withdrawn): A method of manufacturing a semiconductor device, comprising:

introducing an impurity of a first conductivity type into a semiconductor substrate;

forming a tunnel oxide film and a floating gate in a memory cell region;

forming a first gate insulating film for a high voltage transistor in a peripheral circuit region;

forming a second gate insulating film for a low voltage transistor, said second gate insulating film being thinner than said first gate insulating film;

forming an interlayer insulating film for a memory cell;

stacking conductive materials forming a control gate and a floating gate, followed by selectively patterning by etching said control gate, said interlayer insulating film, and said floating gate successively;

selectively patterning the gate electrode of a peripheral circuit region;

introducing an impurity of a second conductivity type into the memory cell region and

the first MOS transistor region included in the peripheral circuit of the semiconductor substrate;

depositing a first side wall material;

forming a first side wall on the side surface of said gate electrode by selectively etching said first side wall material layer by an anisotropic etching;

introducing an impurity of a first conductivity type into the second MOS transistor region of the semiconductor substrate;

introducing an impurity into the first MOS transistor region of the semiconductor substrate in a concentration higher than that in the impurity diffusion layer of the second conductivity type;

depositing a second side wall material and a third side wall material differing from said second side wall material;

forming a third side wall on the side surface of the second side wall by selectively etching said third side wall material by an anisotropic etching;

introducing an impurity into the second MOS transistor region of the semiconductor substrate in a concentration higher than that in said impurity diffusion layer of the first conductivity type;

removing said third side wall;

depositing an interlayer insulating film on the entire surface of the substrate;

selectively forming contact holes in said interlayer insulating film;

forming at least a single metal wiring; and

forming an insulating film on said metal wiring.